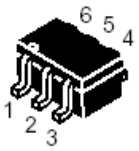
Silicon PNP Epitaxial Planer Transistor

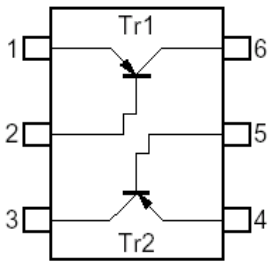
L4401DW1T1



SC88

MAXIMUM RATINGS

Parameter	Symbol	Ratings	Unit
Collector-Emitter Voltage	V_{CEO}	-50	V
Collector-Base Voltage	V_{CBO}	-60	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector current-continuoun	IC	-150	mAdc



THERMAL CHARATEERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) T_A=25°C	P_D	380	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	328	°C/W
Junction and Storage Temperature	Tj ,Tstg	-55 to +150	°C

DEVICE MARKING

L4401DW1T1=5K

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (IC=-1mA)	V(BR)CEO	-50	-	-	V
Emitter-Base Breakdown Voltage (IE=-50μA)	V(BR)EBO	-6	-	-	V
Collector-Base Breakdown Voltage (IC=-50μA)	V(BR)CBO	-60	-	-	V

Collector Cutoff Current (VCB=-60V)	ICBO	-	-	-0.1	μA
Emitter Cutoff Current (VBE=-6V)	IEBO			-0.1	μA

ON CHARACTERISTICS

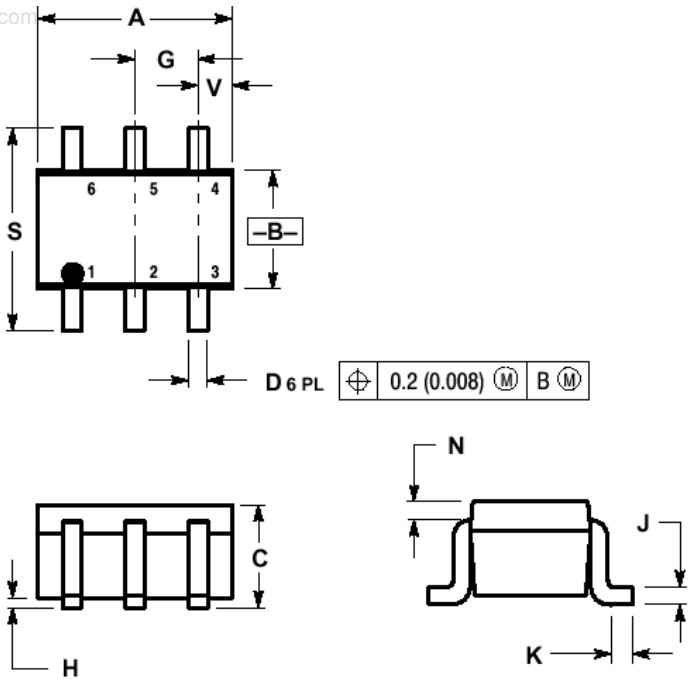
DC Current Gain (IC=-1mA, VCE=-6.0V)	Hfe	120	-	560	
Collector-Emitter Saturation Voltage (IC=-50mA,IB=-5mA)	VCE(SAT)	-	-	-0.5	V

SMALL-SIGNAL CHARACTERISTICS

Current-Gain-Bandwidth Product (VCE = -12.0V; IE =2.0 mA,f=300MHZ)	Ft	-	140	-	MHz
Output Capacitance(VCB=-12V,f=1.0MHz)	Cobo	-	4	5	Pf

PACKAGE DIMENSIONS

SC-88



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026BSC		0.65BSC	
H	—	0.004	—	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20
V	0.012	0.016	0.30	0.40